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INTEGRATED CIRCUIT PACKAGE WITH DIAMOND HEAT SINK

BACKGROUND OF THE INVENTION

The ever-increasing demand for smaller, higher performance information systems has lead to the adoption of the integrated circuit ("IC") as the information processing center of the modern computer. These integrated circuits, or chips, are typically housed within standard ceramic, plastic or metal packages and carry information between the chip and other information processing units within the system.

In one type of plastic encapsulated dual in-line package, such as the package 1 shown in Figure 1, an integrated circuit chip 2 having a plurality of chip bonding pads 3 at its perimeter is fastened to a die substrate 4 which is held by two tie bars 5 embedded in thermoplastic molding compound 6, such as a polyamide. A plurality of metal legs, or leads 7 are also embedded in the plastic compound 6 with (typically) nickel-plated wire bonding pads 8 at their inner ends. The leads 7 and substrate 4 are parts which

have been separated from a lead frame in the course of assembly of the package 1. Lead wires 9 are bonded to the pads 3 and the bonding pads 8 of the leads 7 to connect the chip 2 to the leads 7, which provide connection means to other circuit components.

5 Because electrical inefficiencies in the chip generate heat, the temperature of both the chip 2 and other parts of the package supporting the chip 2 significantly rise during use. It is known that such elevated temperatures can degrade the system's performance. For example, because many of the system's critical
10 processes rely on kinetic phenomena which become accelerated by increased temperature, failures in metallization and bonded interfaces occur during extended use. Accordingly, heat production by the chip, often termed "thermal density", has become a
15 significant design consideration which threatens to limit the further miniaturization of information systems within reasonable cost constraints.

Conventional treatment of the thermal density problem has met with limited success. For example, in the prior art design shown in Figure 1, heat generated by the chip is dissipated through the
20 plastic molding, the die pads and the bonding wires connecting the chip and the legs of the lead frame. However, each of these thermal conduits is only marginally effective. In particular, the wires are poor thermal conduits because they have a small cross section (i.e., about 0.002 inch thickness). The die pads, while



having a good cross section (i.e., about 0.010 inch thickness) are ineffective thermal conduits because they are truncated at each end of the IC package, and so there are no metal thermal paths available to the outside after the IC molding process. The plastic molding has an extremely low thermal conductivity. One present improvement in thermal dissipation connects a more thermally conductive, high surface area material (known as a "heat spreader") to the chip. Although heat spreaders succeed in dissipating hot spots on the chip, they do not significantly assist in removing heat from the package as a whole. Another present improvement involves blowing air across either the chip or attached heat spreader, thereby removing heat convectively from the package. Although this improvement succeeds in removing more heat from the package, it adds cost and requires geometry changes in the area around the package.

Therefore, it is the object of the present invention to provide a package which can provide electrical connection between the chip and the lead frame, yet still maintain the chip at low temperatures.

SUMMARY OF THE INVENTION

In accordance with the present invention, there is provided a plastic encapsulated integrated circuit package comprising:

- a) a thermally conductive, electrically resistive base,
- b) an integrated circuit mounted on the base,



c) a plurality of legs in electrical connection with the integrated circuit, and
wherein the base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

Also in accordance with the present invention, there is provided an integrated circuit package comprising:

- a) an integrated circuit,
- b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and
- c) a diamond film base,

wherein the diamond film base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

DESCRIPTION OF THE FIGURES

Figure 1 is an elevated perspective view of a conventional dual in-line integrated circuit package (DIP).

Figure 2 is an elevated perspective view of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

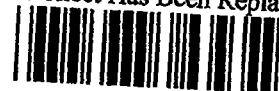
It has been found that mounting a conventional chip on a thermally conductive, electrically resistive substrate (such as diamond film) and providing intimate thermal contact of it with leads allows each of the leads to be used as a direct conduit for



thermal dissipation. Because these leads have thicknesses of about 0.010 inches, they possess a much greater cross-section than the conventional wires, and are therefore more thermally conductive than the plastic encapsulant, the present invention provides for increased heat dissipation from the entire package yet does not interfere with its electrical properties.

For the purposes of the present invention, "intimate thermal contact" means that the thermal conductivity of the interface connecting the device die pad to the lead exceeds 2 W/cm K, so that there is essentially no thermal resistance provided by any gap therebetween. Preferably, the base touches both the leads and the chip.

Any substrate having a thermal conductivity of at least about 2 W/cm K and an electrical resistivity of at least about 10^6 ohm-cm at 10 V dc can be used as the thermally conductive, electrically resistive base of the present invention. These substrates include, but are not limited to, diamond, aluminum nitride, beryllia, diamond-coated substrates, and insulator-clad metals. Preferably, the thermal conductivity of the base is at least about 6 W/cm K, more preferably at least about 10 W/cm K. Preferably, the electrical resistivity of the base is at least about 10^8 ohm-cm, more preferably exceeds 10^{10} ohm-cm. The thickness of the base may be between about 100 and about 500 μ m, preferably between about 150 and 200 μ m.



Most preferably, the base is diamond film because it is both an excellent thermal conductor and an excellent electrical insulator. Such diamond film can be any high thermal conductivity diamond (free standing or coating). In some embodiments, the base is a diamond film having a thermal conductivity of at least about 10 W/cm K and an electrical resistivity of at least about 10 E10 ohm-cm. Typically, the diamond film is chemically vapor deposited (CVD) diamond which has a thickness of between about 150 and about 200 microns. Because the diamond film can be so thin, its utilization in the present invention offers a design advantage in that it can be incorporated into conventional system designs without a significant change in the package geometry.

In one embodiment of the present invention, as shown in Figure 2, there is provided a plastic encapsulated¹² package²⁴ comprising a chip 11 having die pads 12 which is mounted upon a diamond substrate 20. Leads or legs 13 having leg connection bonding pads 14 are not only placed in electrical connection with chip 11 via wires 16, they are also placed in intimate thermal contact with diamond film 20 by virtue of their abutment thereto. The entire package is encapsulated in plastic molding 90, save one end of each leg. Because diamond film is an excellent electrical insulator, its presence does not effect the transmission of information between chip 11 and legs 13. Because diamond film is also an excellent thermal conductor, heat generated within chip 11 flows through the



diamond film and into each of the eight legs 13 and subsequently
out of the package ²⁴99. In contrast to the prior art design shown ✓
in Figure 1, wherein heat generated by the chip is dissipated
directly (and poorly) only through thin wires and through the
5 plastic molding, the present invention allows heat from the
substrate to be dissipated not only through the thin wires and
plastic molding but also directly through each of the wide leads
13. Because the present invention presents many more avenues for
heat dissipation than the conventional design, it will dissipate
10 heat much faster. Thermal analysis of the legs and encapsulant
reveals that the copper leads have a thermal conductivity of about
228 BTU/(hr ft F) while the polyamide has a thermal conductivity of
only about 0.19 BTU/(hr ft F). Since the thermal conductivity of
the legs are about 1000 times superior to that of the encapsulant,
15 it is contemplated that the advantage of the present invention
increases essentially directly with the number of legs in the
package.

In one embodiment of the present invention containing 24 legs,
finite element analysis revealed that the T_{ja} (i.e., the
20 temperature differential between the device junction and the
ambient temperature) was only about 60 degrees C. In contrast, the
 T_{ja} for a comparable conventional IC package was about 400 C for
the same power input.

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The method by which the diamond film is attached to the chip can be any conventional attachment means, including soldering, clamping, bonding agents, and silver loaded epoxies. Similarly, the method by which the diamond film is attached to the legs of the package can be any conventional attachment means, including clamping, soldering, bonding agents, silver loaded epoxies, and brazing.

Any conventional chip and lead frame design can be used with the present invention as long as the design allows for a diamond film to be in intimate thermal contact with both the chip and the legs of the lead frame. Conventional chips include integrated circuits and discrete active devices such as transistors and diodes. Conventional package designs include both plastic and ceramic DIP, SIP, PGA, QFP, BGA and LCC designs. When another thermally conductive, electrically resistive substrate other than diamond is used for a die pad, the IC package of the present invention is plastic encapsulated.

Because the thermally conductive, electrically resistive base of the present invention provides for greater heat dissipation, the IC packages of the present invention can tolerate larger amounts of power than the standard package without exceeding the critical device junction temperature. In particular, the present invention provides an improved JEDEC package capable of dissipating up to at least about 600% more power than the standard JEDEC package in



forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of 125 C.

In one embodiment, finite element analysis revealed that a 24 pin DIP of the present invention was capable of dissipating about 12

5 watts of power in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of 125 C. In contrast, the standard JEDEC 24 pin DIP could dissipate only 1.6 watts.

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I Claim:

1. A plastic encapsulated integrated circuit package comprising:

- 5 a) a thermally conductive, electrically resistive base,
b) an integrated circuit mounted on the base,
10 c) a plurality of legs in electrical connection with the integrated circuit, and

wherein the base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

15 2. The package of claim 1 wherein the base has a thermal conductivity of at least about 6 W/cm K.

20 3. The package of claim 2 wherein the base has a thermal conductivity of at least about 10 W/cm K.

4. The package of claim 3 wherein the base has an electrical resistivity of at least about 18 E8 ohm cm.

25 5. The package of claim 4 wherein the base has an electrical resistivity of at least about 10 E10 ohm cm.

30 6. The package of claim 5 wherein the base has a thickness of between about 100 and about 500 um.

7. The package of claim 6 wherein the base has a thickness of between about 150 and about 200 um.

35 8. The package of claim 7 wherein the base is selected from the group consisting of diamond, aluminum nitride, beryllia, diamond-coated substrates and insulator clad metals.

9. The package of claim 8 wherein the base is diamond.

40 10. The package of claim 9 wherein the diamond has a thickness of between about 150 and about 200 microns.

45 11. The package of claim 10 wherein the package has a design selected from the group consisting of the SIP, DIP, LCC, QFP, and PGA designs.





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12. The package of claim 11 wherein the package has a DIP design.

13. The package of claim 12 capable of dissipating 2 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

14. The package of claim 12 capable of dissipating 5 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

15. The package of claim 12 capable of dissipating 8 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

16. The package of claim 12 capable of dissipating 10 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

17. The package of claim 12 capable of dissipating 12 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

18. An integrated circuit package comprising:

a) an integrated circuit,

b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and

c) a diamond film base,

wherein the diamond film base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

19. The package of claim 18 wherein the base has a thermal conductivity of at least about 6 W/cm K.

20. The package of claim 19 wherein the base has a thermal conductivity of at least about 10 W/cm K.

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21 The package of claim 20 wherein the base has an electrical resistivity of at least about 18×10^8 ohm cm.

22. The package of claim 21 wherein the base has an electrical resistivity of at least about 10×10^{10} ohm cm.

23. The package of claim 22 wherein the base has a thickness of between about 100 and about 500 μm .

24. The package of claim 23 wherein the base has a thickness of between about 150 and about 200 μm .

25. The package of claim 24 wherein the diamond has a thickness of between about 150 and about 200 microns.

26. The package of claim 25 wherein the package has a design selected from the group consisting of the SIP, DIP, LCC, QFP, and PGA designs.

27. The package of claim 26 wherein the package has a DIP design.

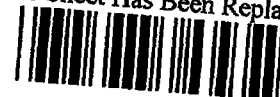
28. The package of claim 27 capable of dissipating 2 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C .

29. The package of claim 28 capable of dissipating 5 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C .

30. The package of claim 29 capable of dissipating 8 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C .

31. The package of claim 30 capable of dissipating 10 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C .

32. The package of claim 31 capable of dissipating 12 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C .



33. The package of claim 28 wherein the package is encapsulated in plastic.

5 34. The package of claim 28 wherein the package is encapsulated in ceramic.

10 35. A 24 pin DIP capable of dissipating 2 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.

15 36. An IC package capable of dissipating at least about 100% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.

20 37. The IC package of claim 36 capable of dissipating at least about 300% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.

25 38. The IC package of claim 36 capable of dissipating at least about 600% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.



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ABSTRACT:

A JEDEC IC package comprising:

a) an integrated circuit,

b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and

c) a diamond film,

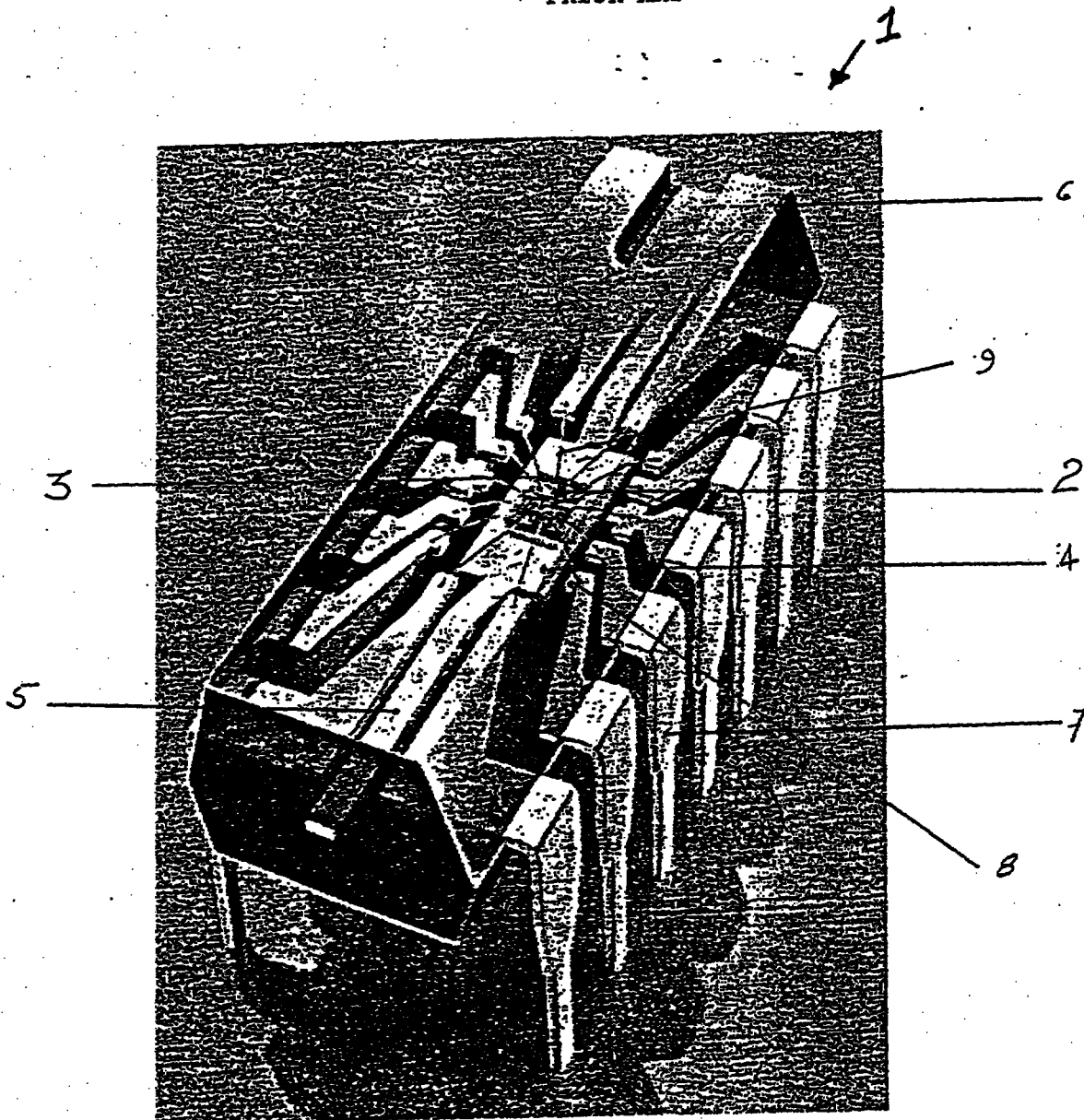
wherein the diamond film is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

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FIGURE 1

PRIOR ART



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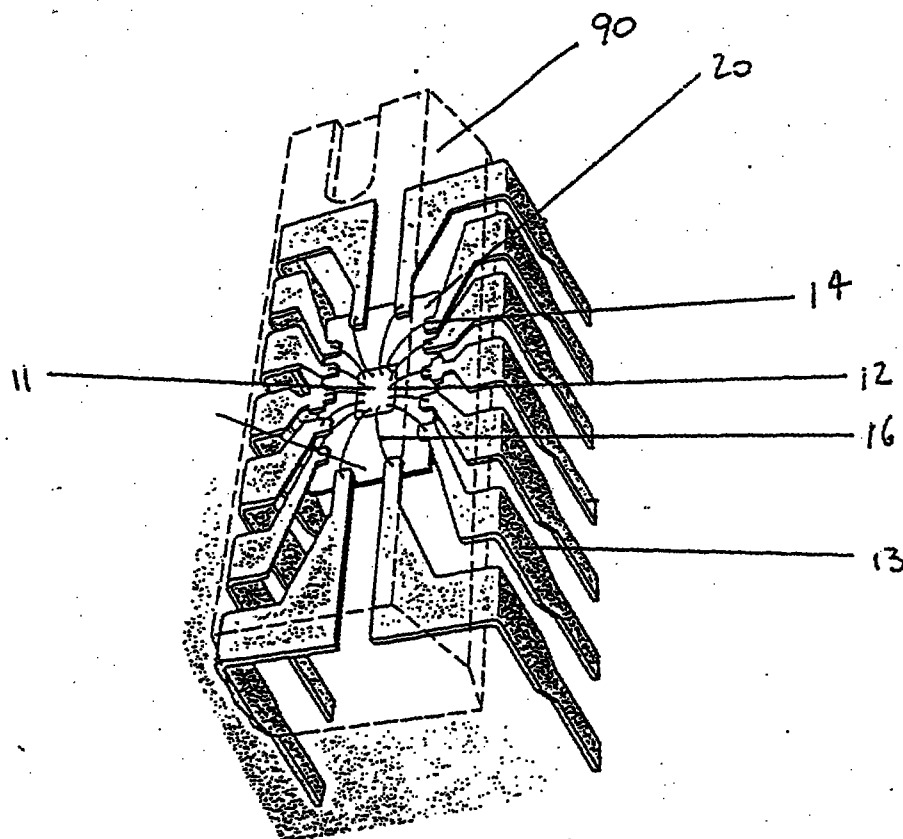


FIGURE 2

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INTEGRATED CIRCUIT PACKAGE WITH DIAMOND HEAT SINK

BACKGROUND OF THE INVENTION

The ever-increasing demand for smaller, higher performance information systems has lead to the adoption of the integrated circuit ("IC") as the information processing center of the modern computer. These integrated circuits, or chips, are typically housed within standard ceramic, plastic or metal packages and carry information between the chip and other information processing units within the system.

In one type of plastic encapsulated dual in-line package, such as the package 1 shown in Figure 1, an integrated circuit chip 2 having a plurality of chip bonding pads 3 at its perimeter is fastened to a die substrate 4 which is held by two tie bars 5 embedded in thermoplastic molding compound 6, such as a polyamide.

A plurality of metal legs, or leads 7 are also embedded in the plastic compound 6 with (typically) nickel-plated wire bonding pads 8 at their inner ends. The leads 7 and substrate 4 are parts which

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have been separated from a lead frame in the course of assembly of the package 1. Lead wires 9 are bonded to the pads 3 and the bonding pads 8 of the leads 7 to connect the chip 2 to the leads 7, which provide connection means to other circuit components.

Because electrical inefficiencies in the chip generate heat, the temperature of both the chip 2 and other parts of the package supporting the chip 2 significantly rise during use. It is known that such elevated temperatures can degrade the system's performance. For example, because many of the system's critical processes rely on kinetic phenomena which become accelerated by increased temperature, failures in metallization and bonded interfaces occur during extended use. Accordingly, heat production by the chip, often termed "thermal density", has become a significant design consideration which threatens to limit the further miniaturization of information systems within reasonable cost constraints.

Conventional treatment of the thermal density problem has met with limited success. For example, in the prior art design shown in Figure 1, heat generated by the chip is dissipated through the plastic molding, the die pads and the bonding wires connecting the chip and the legs of the lead frame. However, each of these thermal conduits is only marginally effective. In particular, the wires are poor thermal conduits because they have a small cross section (i.e., about 0.002 inch thickness). The die pads, while

having a good cross section (i.e., about 0.010 inch thickness) are ineffective thermal conduits because they are truncated at each end of the IC package, and so there are no metal thermal paths available to the outside after the IC molding process. The plastic molding has an extremely low thermal conductivity. One present improvement in thermal dissipation connects a more thermally conductive, high surface area material (known as a "heat spreader") to the chip. Although heat spreaders succeed in dissipating hot spots on the chip, they do not significantly assist in removing heat from the package as a whole. Another present improvement involves blowing air across either the chip or attached heat spreader, thereby removing heat convectively from the package. Although this improvement succeeds in removing more heat from the package, it adds cost and requires geometry changes in the area around the package.

Therefore, it is the object of the present invention to provide a package which can provide electrical connection between the chip and the lead frame, yet still maintain the chip at low temperatures.

SUMMARY OF THE INVENTION

In accordance with the present invention, there is provided a plastic encapsulated integrated circuit package comprising:

- a) a thermally conductive, electrically resistive base,
- b) an integrated circuit mounted on the base,

c) a plurality of legs in ⁴ electrical connection with the integrated circuit, and
wherein the base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

Also in accordance with the present invention, there is provided an integrated circuit package comprising:

- a) an integrated circuit,
- b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and
- c) a diamond film base,

wherein the diamond film base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

DESCRIPTION OF THE FIGURES

Figure 1 is an elevated perspective view of a conventional dual in-line integrated circuit package (DIP).

Figure 2 is an elevated perspective view of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

It has been found that mounting a conventional chip on a thermally conductive, electrically resistive substrate (such as diamond film) and providing intimate thermal contact of it with leads allows each of the leads to be used as a direct conduit for

thermal dissipation. Because these leads have thicknesses of about 0.010 inches, they possess a much greater cross-section than the conventional wires, and are therefore more thermally conductive than the plastic encapsulant, the present invention provides for increased heat dissipation from the entire package yet does not interfere with its electrical properties.

For the purposes of the present invention, "intimate thermal contact" means that the thermal conductivity of the interface connecting the device die pad to the lead exceeds 2 W/cm K, so that there is essentially no thermal resistance provided by any gap therebetween. Preferably, the base touches both the leads and the chip.

Any substrate having a thermal conductivity of at least about 2 W/cm K and an electrical resistivity of at least about $10 E6$ ohm-cm at 10 V dc can be used as the thermally conductive, electrically resistive base of the present invention. These substrates include, but are not limited to, diamond, aluminum nitride, beryllia, diamond-coated substrates, and insulator-clad metals. Preferably, the thermal conductivity of the base is at least about 6 W/cm K, more preferably at least about 10 W/cm K. Preferably, the electrical resistivity of the base is at least about $10E8$ ohm-cm, more preferably exceeds $10 E10$ ohm-cm. The thickness of the base may be between about 100 and about 500 μm , preferably between about 150 and 200 μm .

Most preferably, the base is ⁶diamond film because it is both an excellent thermal conductor and an excellent electrical insulator. Such diamond film can be any high thermal conductivity diamond (free standing or coating). In some embodiments, the base is a diamond film having a thermal conductivity of at least about 10 W/cm K and an electrical resistivity of at least about 10 E10 ohm-cm. Typically, the diamond film is chemically vapor deposited (CVD) diamond which has a thickness of between about 150 and about 200 microns. Because the diamond film can be so thin, its utilization in the present invention offers a design advantage in that it can be incorporated into conventional system designs without a significant change in the package geometry.

In one embodiment of the present invention, as shown in Figure 2, there is provided a plastic encapsulated ¹²package ²⁴comprising a chip 11 having die pads 12 which is mounted upon a diamond substrate 20. Leads or legs 13 having leg connection bonding pads 14 are not only placed in electrical connection with chip 11 via wires 16, they are also placed in intimate thermal contact with diamond film 20 by virtue of their abutment thereto. The entire package is encapsulated in plastic molding 90, save one end of each leg. Because diamond film is an excellent electrical insulator, its presence does not effect the transmission of information between chip 11 and legs 13. Because diamond film is also an excellent thermal conductor, heat generated within chip 11 flows through the

diamond film and into each of the eight legs 13 and subsequently out of the package ²⁴99. In contrast to the prior art design shown in Figure 1, wherein heat generated by the chip is dissipated directly (and poorly) only through thin wires and through the plastic molding, the present invention allows heat from the substrate to be dissipated not only through the thin wires and plastic molding but also directly through each of the wide leads 13. Because the present invention presents many more avenues for heat dissipation than the conventional design, it will dissipate heat much faster. Thermal analysis of the legs and encapsulant reveals that the copper leads have a thermal conductivity of about 228 BTU/(hr ft F) while the polyamide has a thermal conductivity of only about 0.19 BTU/(hr ft F). Since the thermal conductivity of the legs are about 1000 times superior to that of the encapsulant, it is contemplated that the advantage of the present invention increases essentially directly with the number of legs in the package.

In one embodiment of the present invention containing 24 legs, finite element analysis revealed that the T_{ja} (i.e., the temperature differential between the device junction and the ambient temperature) was only about 60 degrees C. In contrast, the T_{ja} for a comparable conventional IC package was about 400 C for the same power input.

The method by which the diamond film is attached to the chip can be any conventional attachment means, including soldering, clamping, bonding agents, and silver loaded epoxies. Similarly, the method by which the diamond film is attached to the legs of the package can be any conventional attachment means, including clamping, soldering, bonding agents, silver loaded epoxies, and brazing.

Any conventional chip and lead frame design can be used with the present invention as long as the design allows for a diamond film to be in intimate thermal contact with both the chip and the legs of the lead frame. Conventional chips include integrated circuits and discrete active devices such as transistors and diodes. Conventional package designs include both plastic and ceramic DIP, SIP, PGA, QFP, BGA and LCC designs. When another thermally conductive, electrically resistive substrate other than diamond is used for a die pad, the IC package of the present invention is plastic encapsulated.

Because the thermally conductive, electrically resistive base of the present invention provides for greater heat dissipation, the IC packages of the present invention can tolerate larger amounts of power than the standard package without exceeding the critical device junction temperature. In particular, the present invention provides an improved JEDEC package capable of dissipating up to at least about 600% more power than the standard JEDEC package in

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forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of 125 C. In one embodiment, finite element analysis revealed that a 24 pin DIP of the present invention was capable of dissipating about 12 watts of power in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of 125 C. In contrast, the standard JEDEC 24 pin DIP could dissipate only 1.6 watts.



REPLACEMENT SHEET

Date 22 FEB 1996

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I Claim:

1. A plastic encapsulated integrated circuit package comprising:
 - a) a thermally conductive, electrically resistive base,
 - b) an integrated circuit mounted on the base,
 - c) a plurality of legs in electrical connection with the integrated circuit, andwherein the base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.
2. The package of claim 1 wherein the base has a thermal conductivity of at least about 6 W/cm K.
3. The package of claim 2 wherein the base has a thermal conductivity of at least about 10 W/cm K.
4. The package of claim 3 wherein the base has an electrical resistivity of at least about 18 E8 ohm cm.
5. The package of claim 4 wherein the base has an electrical resistivity of at least about 10 E10 ohm cm.
6. The package of claim 5 wherein the base has a thickness of between about 100 and about 500 um.
7. The package of claim 6 wherein the base has a thickness of between about 150 and about 200 um.
8. The package of claim 7 wherein the base is selected from the group consisting of diamond, aluminum nitride, beryllia, diamond-coated substrates and insulator clad metals.
9. The package of claim 8 wherein the base is diamond.
10. The package of claim 9 wherein the diamond has a thickness of between about 150 and about 200 microns.
11. The package of claim 10 wherein the package has a design selected from the group consisting of the SIP, DIP, LCC, QFP, and PGA designs.



12. The package of claim 11 wherein the package has a DIP design.
13. The package of claim 12 capable of dissipating 2 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
14. The package of claim 12 capable of dissipating 5 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
15. The package of claim 12 capable of dissipating 8 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
16. The package of claim 12 capable of dissipating 10 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
17. The package of claim 12 capable of dissipating 12 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
18. An integrated circuit package comprising:
- a) an integrated circuit,
 - b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and
 - c) a diamond film base,
- wherein the diamond film base is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.
19. The package of claim 18 wherein the base has a thermal conductivity of at least about 6 W/cm K.
20. The package of claim 19 wherein the base has a thermal conductivity of at least about 10 W/cm K.

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21. The package of claim 20 wherein the base has an electrical resistivity of at least about $18 \text{ E}8 \text{ ohm cm.}$
22. The package of claim 21 wherein the base has an electrical resistivity of at least about $10 \text{ E}10 \text{ ohm cm.}$
23. The package of claim 22 wherein the base has a thickness of between about 100 and about 500 $\mu\text{m.}$
24. The package of claim 23 wherein the base has a thickness of between about 150 and about 200 $\mu\text{m.}$
25. The package of claim 24 wherein the diamond has a thickness of between about 150 and about 200 microns.
26. The package of claim 25 wherein the package has a design selected from the group consisting of the SIP, DIP, LCC, QFP, and PGA designs.
27. The package of claim 26 wherein the package has a DIP design.
28. The package of claim 27 capable of dissipating 2 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C.
29. The package of claim 28 capable of dissipating 5 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C.
30. The package of claim 29 capable of dissipating 8 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C.
31. The package of claim 30 capable of dissipating 10 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C.
32. The package of claim 31 capable of dissipating 12 watts of energy in forced air with a convection coefficient of about $50 \text{ W/m}^2 \text{ C}$ at 50 C while maintaining a maximum junction temperature of 125 C.



REPLACEMENT SHEET

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33. The package of claim 28 wherein the package is encapsulated in plastic.
34. The package of claim 28 wherein the package is encapsulated in ceramic.
35. A 24 pin DIP capable of dissipating 2 watts of energy in forced air with a convection coefficient of about 50 W/m² C at 50 C while maintaining a maximum junction temperature of 125 C.
36. An IC package capable of dissipating at least about 100% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.
37. The IC package of claim 36 capable of dissipating at least about 300% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.
38. The IC package of claim 36 capable of dissipating at least about 600% more power than its comparable standard JEDEC IC package in forced air with a convection coefficient of about 50 W/m² C at 50 C while still maintaining a maximum junction temperature of at least about 125 C.

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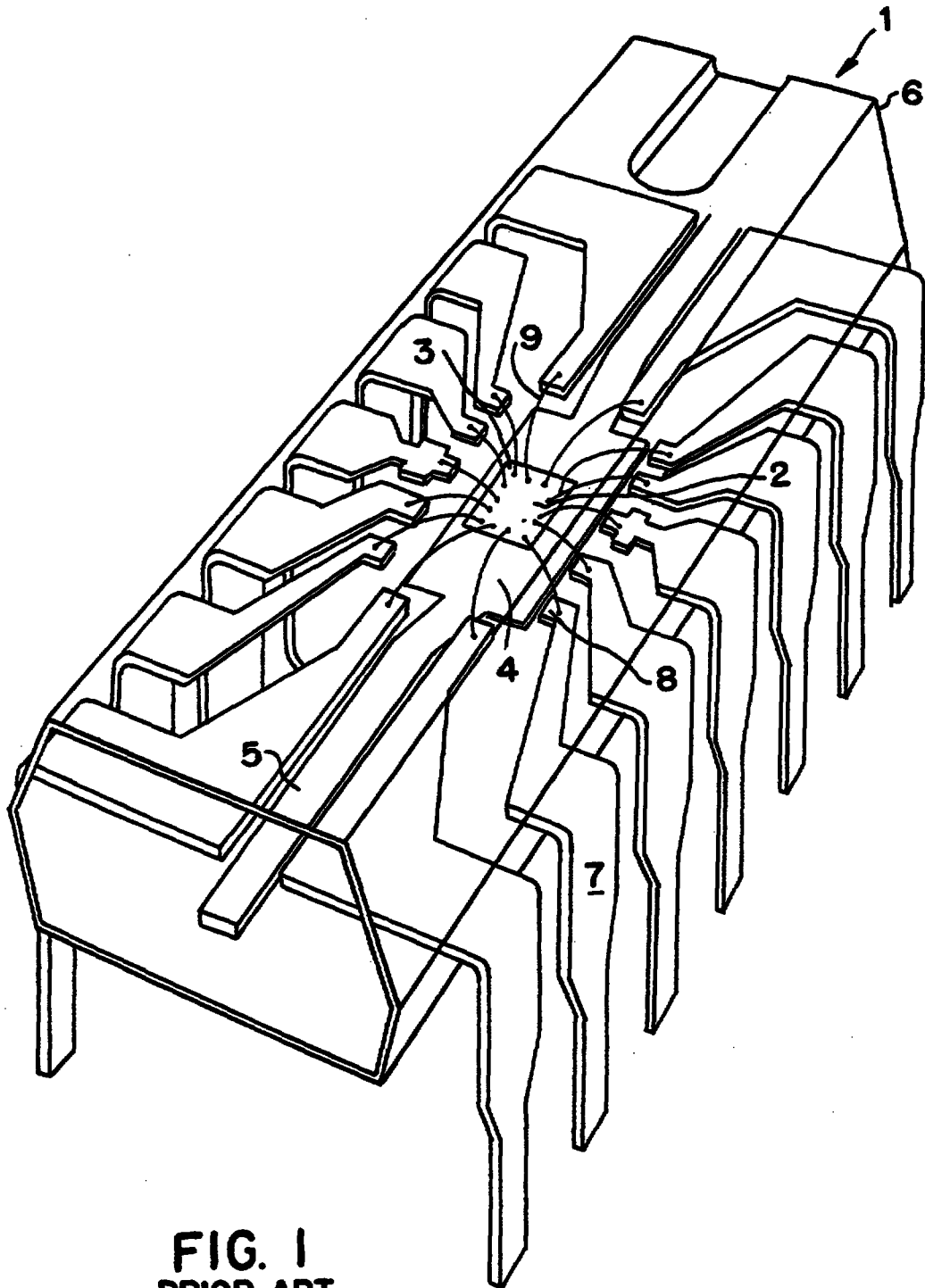


FIG. 1
PRIOR ART

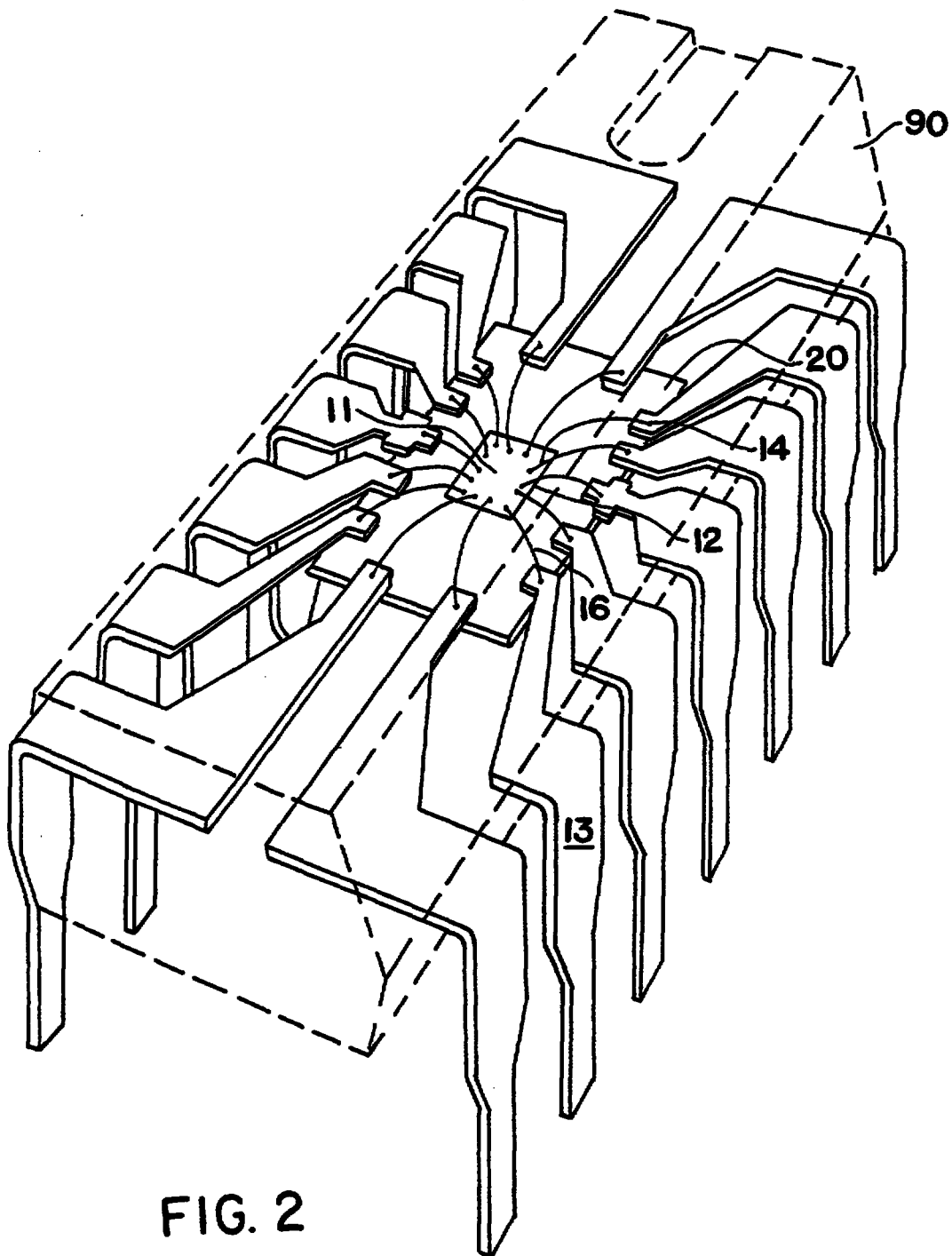


FIG. 2

REPLACEMENT SHEET
Date: 22 FEB 1996

INTEGRATED CIRCUIT PACKAGE WITH DIAMOND HEAT SINK

ABSTRACT:

A JEDEC IC package comprising:

- a) an integrated circuit,
- b) a lead frame having a plurality of legs in electrical connection with the integrated circuit, and
- c) a diamond film,

wherein the diamond film is in intimate thermal contact with both the integrated circuit and the plurality of legs of the lead frame.

Figure 2